

## Product Overview

### NCP5109: MOSFET / IGBT Drivers, Dual Input, High Voltage, High and Low Side, 200 V

For complete documentation, see the data sheet.

The NCP5109 is a High Voltage gate Driver IC providing two outputs for direct drive of 2 N-channel power MOSFETs or IGBTs arranged in a half-bridge configuration version B or any other high-side + low-side configuration version A. It uses the bootstrap technique to insure a proper drive of the High-side power switch. The driver works with 2 independent inputs. NCP5109 = 200V NCP5106 = 600V

### Features

- High Voltage Range: Up to 200 V
- dV/dt Immunity 50 V/nsec
- Gate Drive Supply Range from 10 V to 20 V
- High and Low Drive Outputs
- Output Source / Sink Current Capability 250 mA / 500 mA
- 3.3 V and 5 V Input Logic Compatible
- Up to Vcc Swing on Input Pins
- Matched Propagation Delays Between Both Channels
- Outputs in Phase with the Inputs
- Independent Logic Inputs to Accommodate All Topologies (Version A)

For more features, see the data sheet

### Applications

- Current Fed push-pull converters
- Half and Full Bridge power converters
- Two switch forward power converters

### End Products

- Solid state motor drives

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Power Switch	Number of Outputs	Topology	Isolation Type	V <sub>in</sub> Max (V)	V <sub>cc</sub> Max (V)	Rise Time (ns)	Fall Time (ns)	Drive Source Current Typ (A)	Drive Sink Current Typ (A)	Turn On Prop. Delay Typ (ns)	Turn Off Prop. Delay Typ (ns)	Delay Matching	Package Type
NCP5109ADR2G	0.3987	Pb-free Halide free non AEC-Q and PPAP	Active	MOS FET / IGBT	2	High-Low	Junction Isolation	200	23	85	35	0.25	0.5	100	100	35	SOIC-8
NCP5109AMNTWG	0.5451	Pb-free Halide free non AEC-Q and PPAP	Active	MOS FET / IGBT	2	High-Low	Junction Isolation	200	23	85	35	0.25	0.5	100	100	35	DFN-10
NCP5109BDR2G	0.3987	Pb-free Halide free non AEC-Q and PPAP	Active	MOS FET / IGBT	2	High-Low	Junction Isolation	200	23	85	35	0.25	0.5	100	100	35	SOIC-8
NCP5109BMNTWG	0.4748	Pb-free Halide free non AEC-Q and PPAP	Active	MOS FET / IGBT	2	High-Low	Junction Isolation	200	23	85	35	0.25	0.5	100	100	35	DFN-10

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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